Minos
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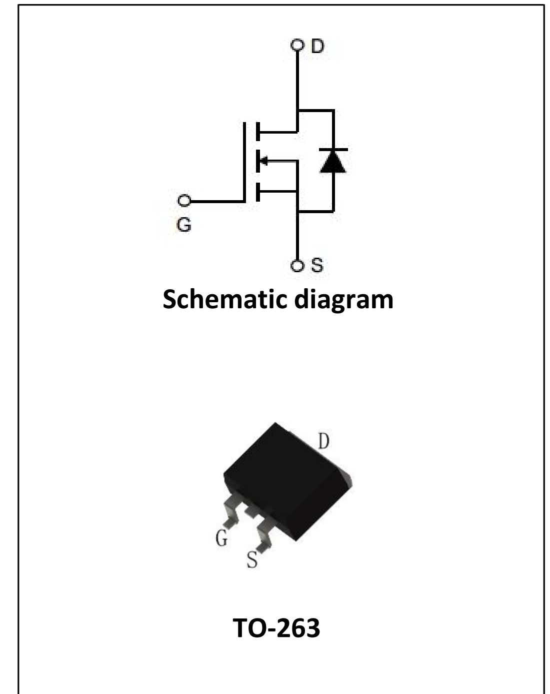
IRF640NS

Silicon N-Channel Power MOSFET

Description

IRF640NS, the silicon N-channel Enhanced MOSFETs, is obtained by advanced MOSFET technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor is suitable device for SMPS, high speed switching and general purpose applications.



KEY CHARACTERISTICS

① V_{DS}=200V,I_D=18A $R_{DS(ON)}$<180mΩ@V_{GS}=10V
② Fast Switching
③ Low Crss
④ 100% avalanche tested Improved dv/dt capability
⑤ RoHS product

APPLICATIONS

① High frequency switching mode power supply

ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing
IRF640NS	TO-263	IRF640NS	Reel

ABSOLUTE RATINGS at TC=25°C,unless otherwise specified

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	200	V
I_D	Continuous Drain Current	18	A
	Continuous Drain Current TC = 100 °C	11	A
I_{DM}	Pulsed Drain Current(Note1)	72	A
V_{GS}	Gate-to-Source Voltage	±30	V
E_{AS}	Single Pulse Avalanche Energy(Note2)	580	mJ
dv/dt	Peak Diode Recovery dv/dt(Note3)	5.0	V/ns
P_D	Power Dissipation TO-220, TO-251,TO-252	130	W
	Derating Factor above 25°C	1.2	W/℃

P_D	Power Dissipation TO-220F	42	W
	Derating Factor above 25°C	0.33	W/℃
T_J，T_{stg}	Operating Junction and Storage Temperature Range	150，–55 to 150	℃
T_L	Maximum Temperature for Soldering	300	℃

Thermal characteristics

Thermal characteristics (No FullPAK) TO-220\TO-251\TO-252

Symbol	Parameter	RATINGS	Units
$R_{\theta JC}$	Junction-to-Case	0.84	℃/W
$R_{\theta JA}$	Junction-to-Ambient	62.5	℃/W

Thermal characteristics (FullPAK) TO-220F

Symbol	Parameter	RATINGS	Units
$R_{\theta JC}$	Junction-to-Case	3.0	℃/W
$R_{\theta JA}$	Junction-to-Ambient	62.5	℃/W

Electrical Characteristics At TC=25°C,unless otherwise specified

OFF Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	V_{GS}=0V, I_D=250µA	200	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Bvdss Temperature Coefficient	ID=250uA, Reference25℃	--	0.25	--	V/℃
I_{DSS}	Drain to Source Leakage Current	V_{DS} =200V, V_{GS}= 0V, T_j = 25℃	--	--	1	µA
		V_{DS} =160V, V_{GS}= 0V, T_j = 125℃	--	--	100	µA
$I_{GSS(F)}$	Gate to Source Forward Leakage	V_{GS} =+30V	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	V_{GS} =-30V	--	--	-100	nA

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ON Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	V_{GS}=10V, I_D=7.5A(Note4)	--	0.13	0.18	Ω
$V_{GS(TH)}$	Gate Threshold Voltage	VDS = VGS, ID = 250μA(Note4)	2.0	--	4.0	V
g_{fs}	Forward Transconductance	VDS=15V, ID =9A(Note4)	--	12	--	S

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
R_g	Gate resistance	f = 1.0MHz	--	2	--	Ω
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V F = 1.0MHz	--	1320	--	PF
C_{oss}	Output Capacitance		--	450	--	
C_{rss}	Reverse Transfer Capacitance		--	130	--	

Switching Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	ID = 18A VDD = 100V VGS = 10V RG =20Ω	--	15	--	ns
T_r	Rise Time		--	52	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	46	--	
t_f	Fall Time		--	37	--	
Q_g	Total Gate Charge	ID =18A VDD =160V VGS = 10V	--	23	--	nC
Q_{gs}	Gate to Source Charge		--	8	--	
Q_{gd}	Gate to Drain (“Miller”)Charge		--	6	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)	T_C=25 °C	--	--	18	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	72	A

V_{SD}	Diode Forward Voltage	I_S=18A, V_{GS}=0V(Note4)	--	--	1.2	V
T_{rr}	Reverse Recovery Time	I_S=18A, T_j = 25°C $d_{IF/dt}$=100A/us, V_{GS}=0V	--	350	--	ns
Q_{rr}	Reverse Recovery Charge		--	3600	--	nC

Note1: Pulse width limited by maximum junction temperature

Note2: L=2.7mH, VDs=50V, Start TJ=25℃

Note3: ISD =18A,di/dt ≤100A/us,VDD≤BVDS, Start TJ=25℃

Note4: Pulse width tp≤300μs, δ≤2%

Characteristics Curves

Figure 1a Safe Operating Area (No FullPAK)	Figure 1b Safe Operating Area (FullPAK)

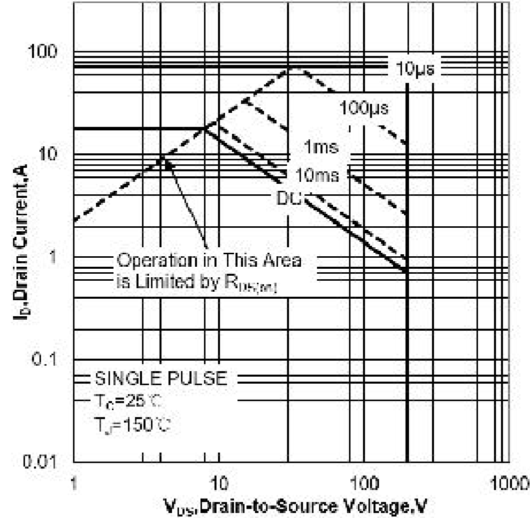
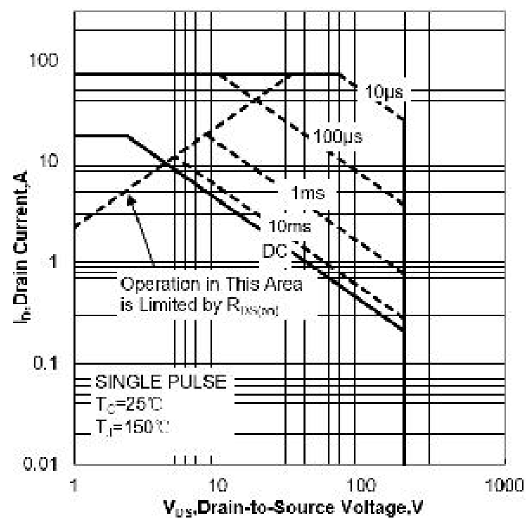

	

Figure 2a Power Dissipation (No FullPAK)	Figure 2b Power Dissipation (FullPAK)

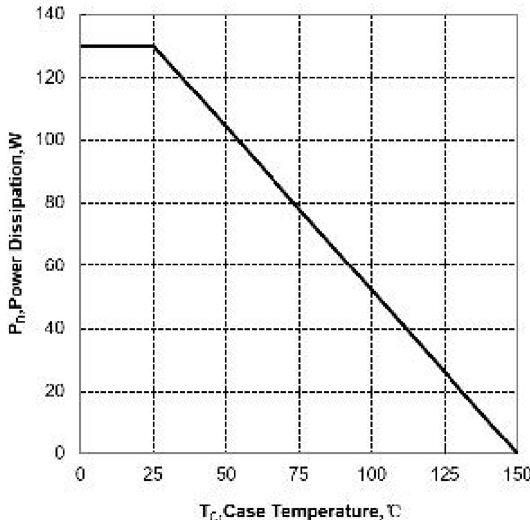
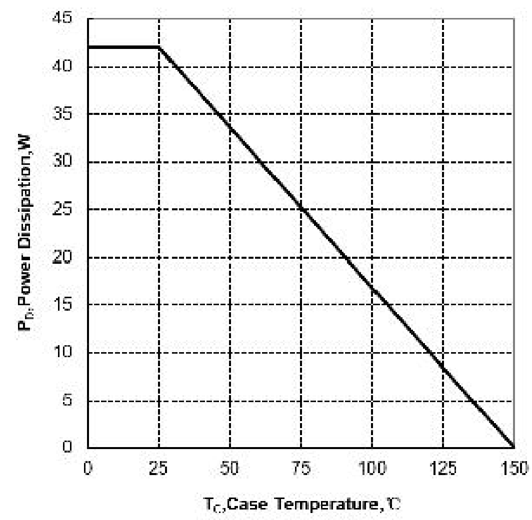

	

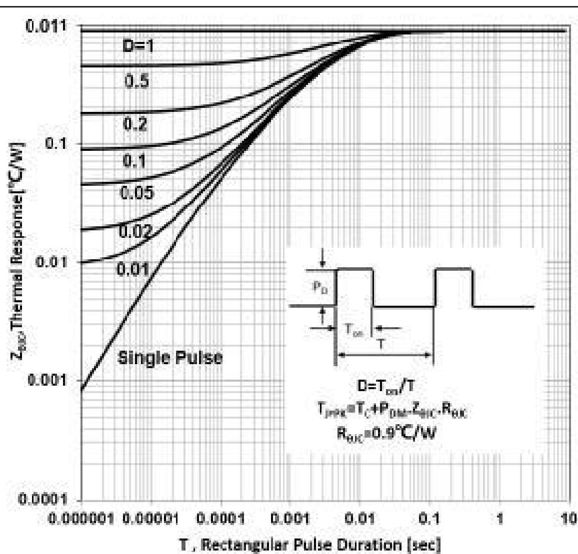
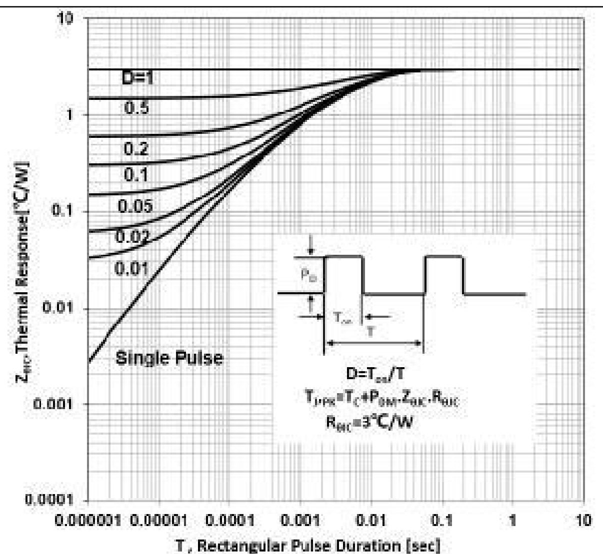
Figure 3a Max Thermal Impendance (No FullPAK)	Figure 3b Max Thermal Impendance (FullPAK)
	

Figure 4 Typical Output Characteristics	Figure 5 Typical Transfer Characteristics

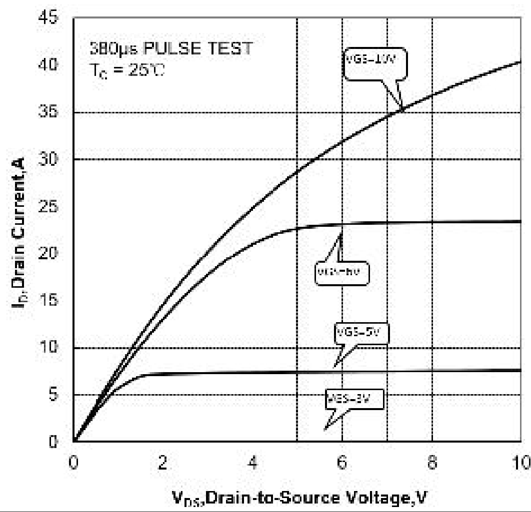
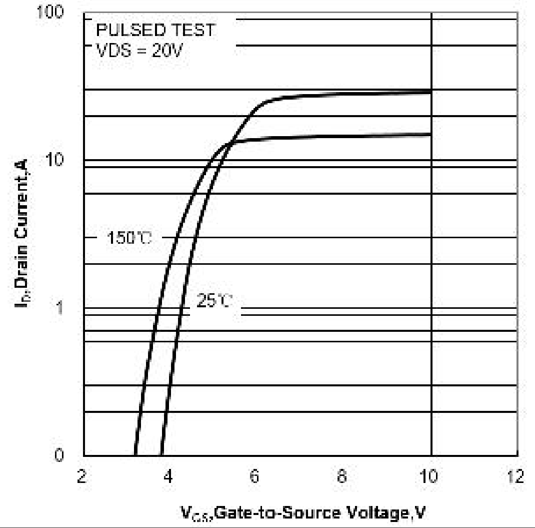

	

Figure 6 Typical Drain to Source ON Resistance vs Drain Current	**Figure 7 Typical Drian to Source on Resistance vs Junction Temperature**

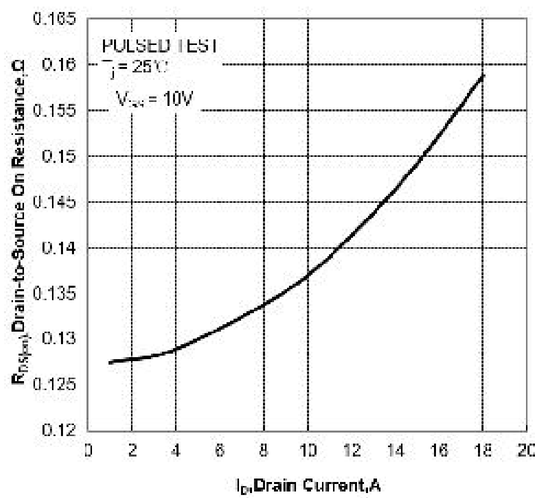
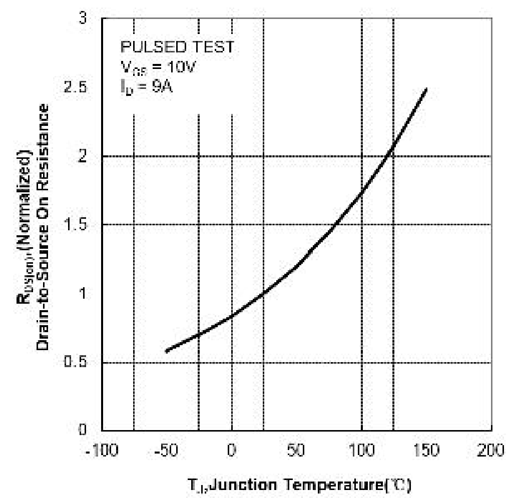

	

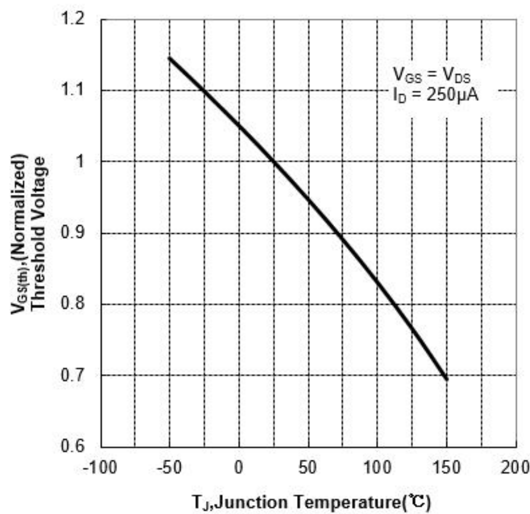
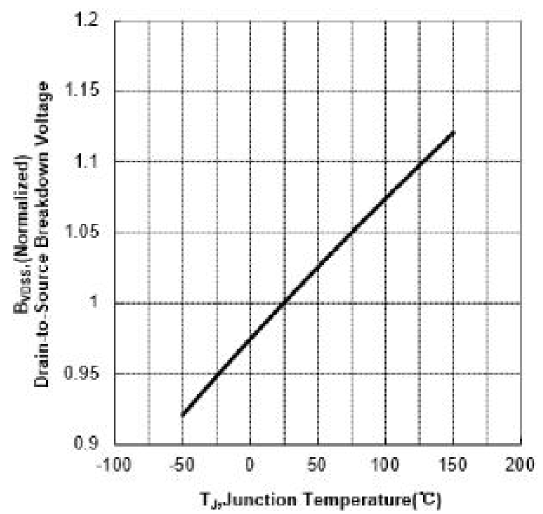
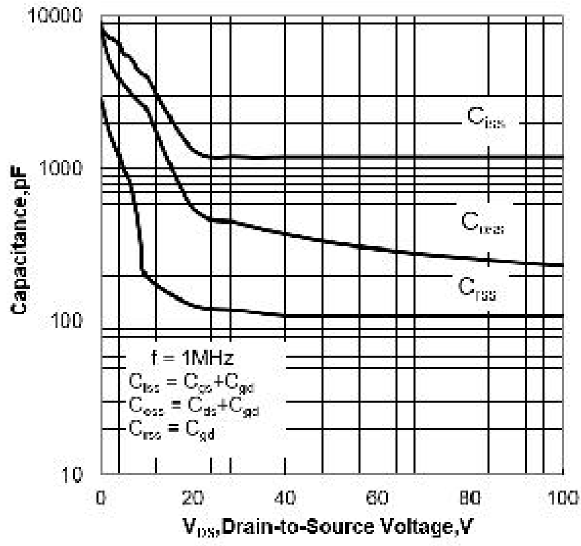
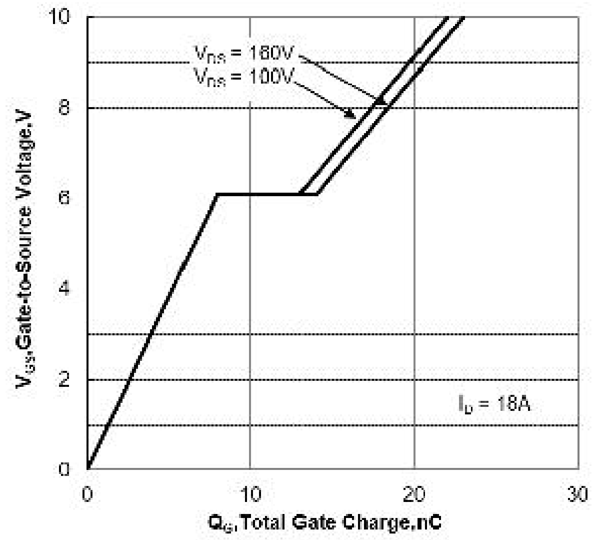
Figure 8 Typical Theshold Voltage vs Junction Temperature	**Figure 9 Typical Breakdown Voltage vs Junction Temperature**
	

Figure 10 Capacitance Characteristics	Figure 11 Gate Charge Characteristics
	

Test Circuit and Waveform

Figure 12 Gate Charge Test Circuit

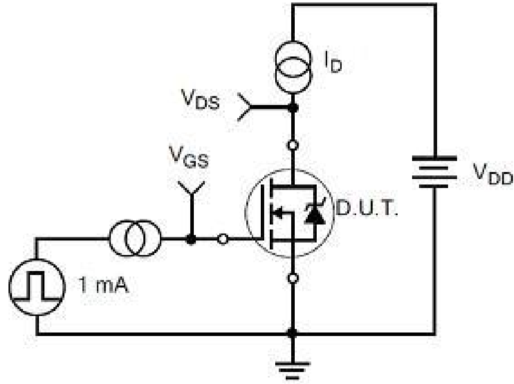


Figure 13 Gate Charge Waveforms

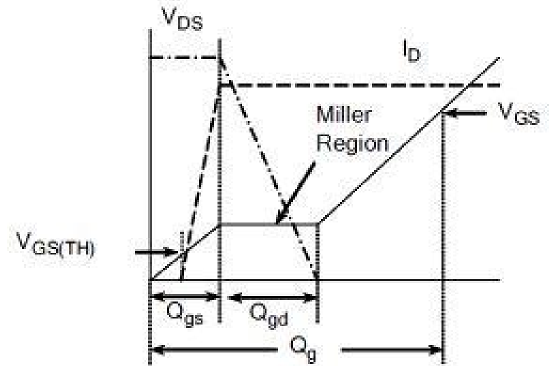


Figure 14 Resistive Switching Test Circuit

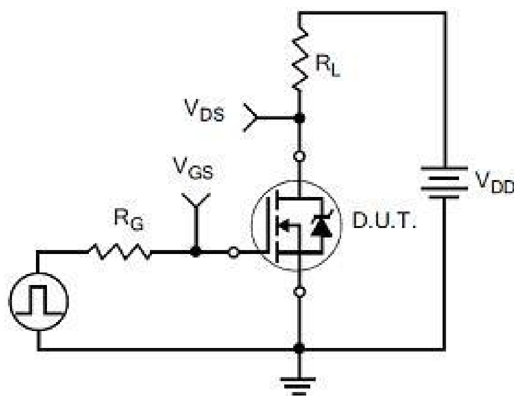


Figure 15 Resistive Switching Waveforms

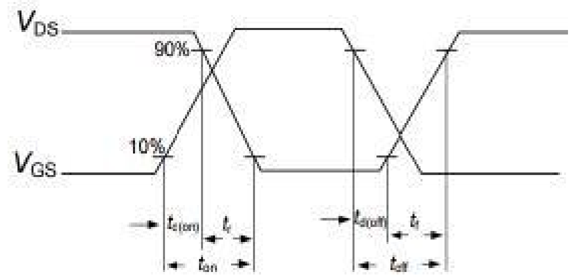


Figure 16 Diode Reverse Recovery Test Circuit

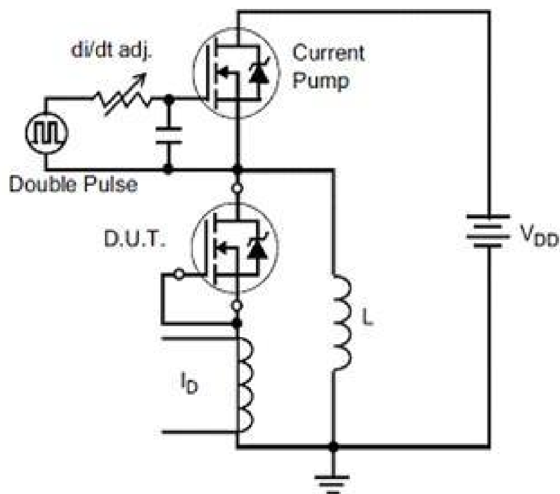


Figure 17 Diode Reverse Recovery Waveform

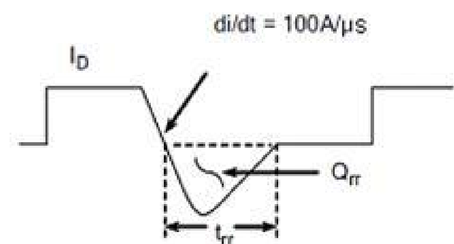
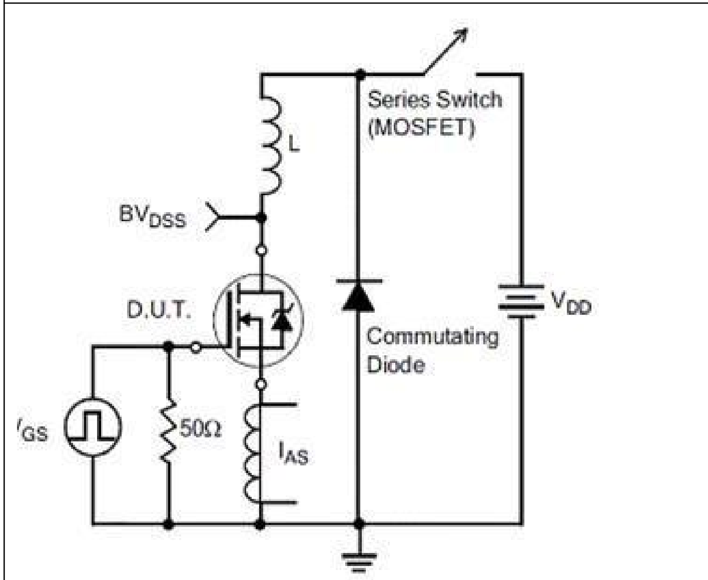
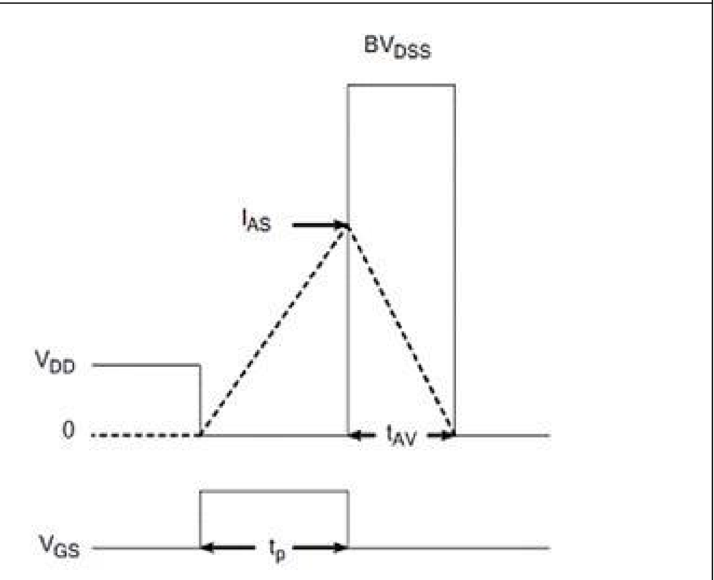
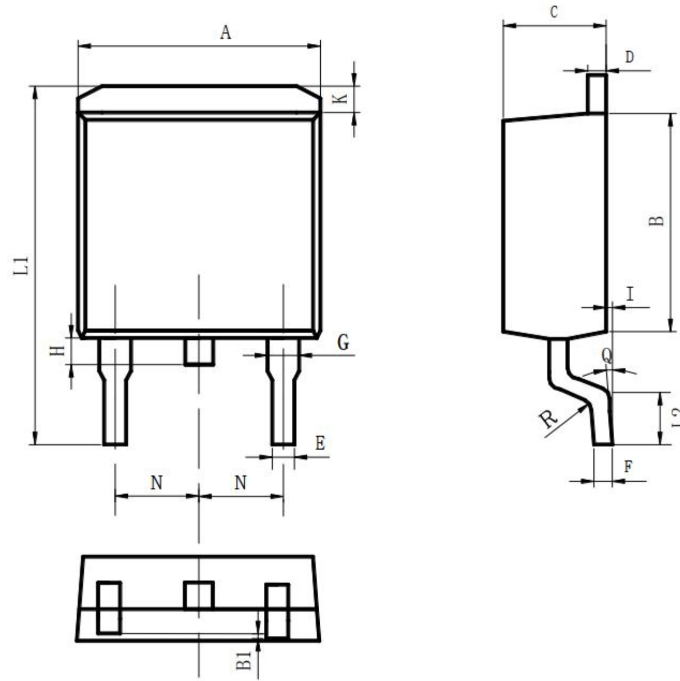


Figure 18 Unclamped Inductive Switching Test Circuit	Figure 19 Unclamped Inductive Switching Waveform
	

Package Description



Items	Values(mm)	
	MIN	MAX
A	9.80	10.40
B	8.90	9.50
B1	0	0.10
C	4.40	4.80
D	1.16	1.37
E	0.70	0.95
F	0.30	0.60
G	1.07	1.47
H	1.30	1.80
K	0.95	1.37
L1	14.50	16.50
L2	1.60	2.30
I	0	0.2
Q	0°	8°
R	0.4	
N	2.39	2.69

TO-263 package

NOTE:

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shenzhen Minos reserves the right to make changes in this specification sheet and is subject to change withoutprior notice.

CONTACT:

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